

1. (Currently Amended) A manufacturing method of manufacturing a semiconductor device having a plurality of wiring layers, said method comprising the steps of:

forming a wiring by a first wiring layer as a pattern by dividing a desired pattern divided into a plurality of patterns, connecting the divided patterns; and exposing them, wherein a position of the a connection of the divided patterns is formed in parallel with the wiring which is formed by the first wiring layer; and

forming a wiring by a second wiring layer having an area which intersects the connecting position by a batch processing of exposure.

4. (Currently Amended) A manufacturing method of manufacturing a solid state image pickup device having pixels each having a photoelectric converting area for converting light into signal charges and a plurality of wiring layers including a first wiring layer and a second wiring layer, said method comprising the steps of:

forming a wiring by the first wiring layer as a pattern by dividing a desired pattern divided into a plurality of patterns, connecting the divided patterns; and exposing them, wherein a position of the a connection of the divided patterns is arranged in parallel with the wiring which is formed by the first wiring layer; and

forming a wiring by the second wiring layer having an area which intersects the connecting position by a batch processing of exposure.

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